first contact area, the second metal layer having a selected area disposed above the first contact area;

a microvia cavity within the selected area being disposed through the second metal layer and through the dielectric layer and extending to the first contact area of the first metal layer; and

a mass of a single conductive material forming a layer upon the selected area of the second metal layer and totally filling the microvia cavity and being in contact with the first contact area of the first metal layer.

2. (PREVIOUSLY AMENDED) The structure of claim 1, wherein the mass of the single conductive material conformally fills the microvia cavity.

3. (PREVIOUSLY AMENDED) The structure of claim 1, wherein the mass of the single conductive material has a planar surface forming a contact pad located parallel to and opposite the first contact area of the first metal layer.

4. (PREVIOUSLY AMENDED) The structure of claim 1, wherein selected area is approximately centered around the first contact area.

5. (PREVIOUSLY AMENDED) The structure of claim 4, wherein the second metal layer within the selected area is approximately centered around the microvia cavity.

6. (PREVIOUSLY AMENDED) The structure of claim 1, wherein the second metal layer within

the selected area is approximately centered around the first contact area.

7. The structure of claim 1, wherein the second metal layer contains a flat copper ring around the microvia cavity.

8. The structure of claim 1, wherein the microvia cavity includes a truncated cone-shaped hole in the dielectric layer.

9. (PREVIOUSLY AMENDED) The structure of claim 1, wherein the mass of the single conductive material comprises at least one of a solder paste, a reflowable solder, a conductive paste, and a conductive adhesive.

20. (PREVIOUSLY AMENDED) An assembly comprising:

a semiconductor chip;

a substrate having a dielectric layer between a first metal layer and a second metal layer, the second metal layer being disposed above the first metal layer, the first metal layer having a first contact area, the second metal layer having a selected area disposed above the first contact area;

a microvia cavity within the selected area being disposed through the second metal layer and through the dielectric layer and extending to the first contact area of the first metal layer; and

a mass of a single conductive material forming a layer upon the selected area of the second metal layer and totally filling the microvia cavity and being in contact with the first